



IXTK200N10L2 Information



For Reference Only

Part Number IXTK200N10L2

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 200A TO-264

Package TO-264-3, TO-264AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXTK200N10L2 Specifications

Manufacturer Part Number IXTK200N10L2 Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-264-3, TO-264AA Series Linear L.2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 200A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 3mA Gate Charge (Qg) (Max) @ Vgs 540nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 23000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1040W (Tc) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA		
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Series Linear L2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 200A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 3mA Gate Charge (Qg) (Max) @ Vgs 540nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 23000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1040W (Tc) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA		Transistors - FETs, MOSFETs - Single
FET Type Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Petaing Temperature Supplier Device Package TO-264 (IXTK) Package / Case N-Channel 100V 2004 To-264-3, TO-264-AA	Package	TO-264-3, TO-264AA
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature Supplier Device Package TO-264 (IXTK) Package / Case MOSFET (Metal Oxide) 100V 100V 200A (Tc) 200A (Tc)	Series	Linear L2?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 200A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 3mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature Supplier Device Package TO-264 (IXTK) Package / Case 100V 200A (Tc) 200A (Tc) 200A (Tc) 200A (Tc) 10V 4.5V @ 3mA 540n © 10V 10V 10V 11 mOhm @ 10V 10V 10V 11 mOhm @ 10V 1040W (Tc) 11 mOhm @ 100A, 10V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 3mA Gate Charge (Qg) (Max) @ Vgs 540nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 23000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 3mA Gate Charge (Qg) (Max) @ Vgs 540nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 23000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1040W (Tc) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 23000pF @ 25V Vgs (Max) #20V FET Feature Power Dissipation (Max) In mohm @ 100A, 10V Operating Temperature Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	Current - Continuous Drain (Id) @ 25°C	200A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 23000pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 23000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	Vgs(th) (Max) @ Id	4.5V @ 3mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1040W (Tc)Rds On (Max) @ Id, Vgs11 mOhm @ 100A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-264 (IXTK)Package / CaseTO-264-3, TO-264AA	Gate Charge (Qg) (Max) @ Vgs	540nC @ 10V
FET Feature - Power Dissipation (Max) 1040W (Tc) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	Input Capacitance (Ciss) (Max) @ Vds	23000pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 11 mOhm @ 100A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	Power Dissipation (Max)	1040W (Tc)
Mounting Type Through Hole Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	Rds On (Max) @ Id, Vgs	11 mOhm @ 100A, 10V
Supplier Device Package TO-264 (IXTK) Package / Case TO-264-3, TO-264AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-264-3, TO-264AA	Mounting Type	Through Hole
	Supplier Device Package	TO-264 (IXTK)
Report errors?	Package / Case	TO-264-3, TO-264AA
		Report errors?

IXTK200N10L2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTK200N10L2 Payment Methods



















IXTK200N10L2 Shipping Methods













If you have any question about IXTK200N10L2, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com